



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
201/	65mΩ @ V _{GS} = 10V	3.4A
30V	$75m\Omega$ @ $V_{GS} = 4.5V$	3.0A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions
- Backlighting
- Load Switch

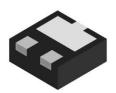
Features and Benefits

- Low On-Resistance
- Low Input/Output Leakage
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

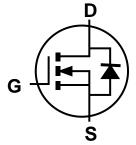
Mechanical Data

- Case: X2-DFN1010-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 4
- Weight: 0.0015 Grams (Approximate)

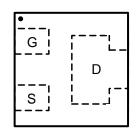




Bottom View



Equivalent Circuit



Pin-out Top View

Ordering Information (Note 4)

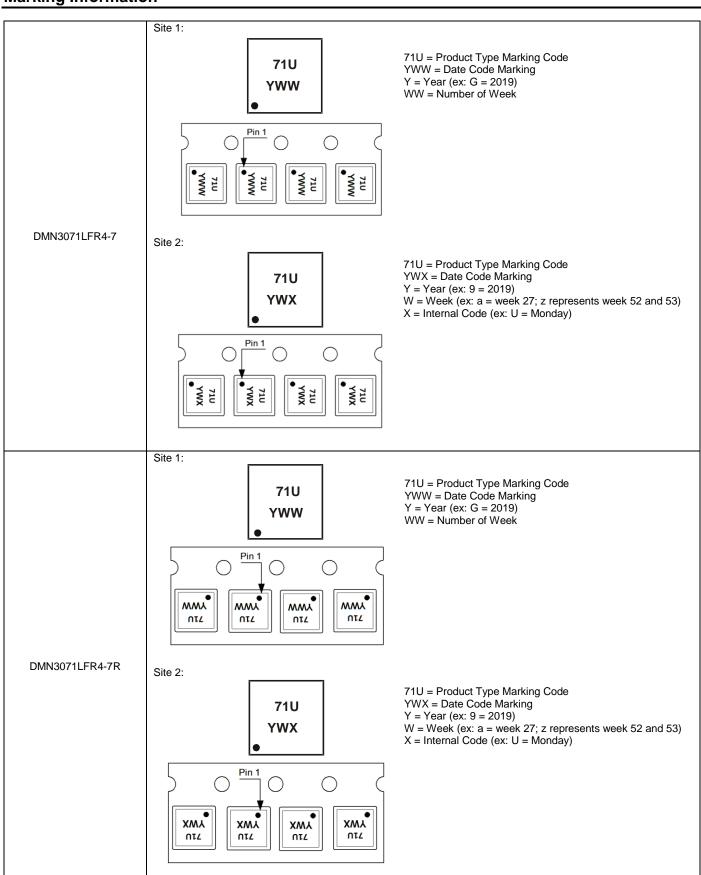
Part Number	Case	Tape Width (mm)	Tape Pitch (mm)	Packaging
DMN3071LFR4-7	X2-DFN1010-3	8	4	3000/Tape & Reel
DMN3071LFR4-7R	X2-DFN1010-3	8	4	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information





Marking Information (Cont.)

Site 1:

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	Н	I	J	K	L	M

Site 2:

Ī	Year	2018	2019	2020	2021	2022	2023	2024	2025
Ī	Code	8	9	0	1	2	3	4	5

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

	Week	1-26	27-52	53
Ī	Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +100^{\circ}C$			I _D	3.4 2.7	А
Maximum Continuous Body Diode Forward Current (I _S	1.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	15	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	221	°C/W
Total Power Dissipation (Note 6)		P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	107	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

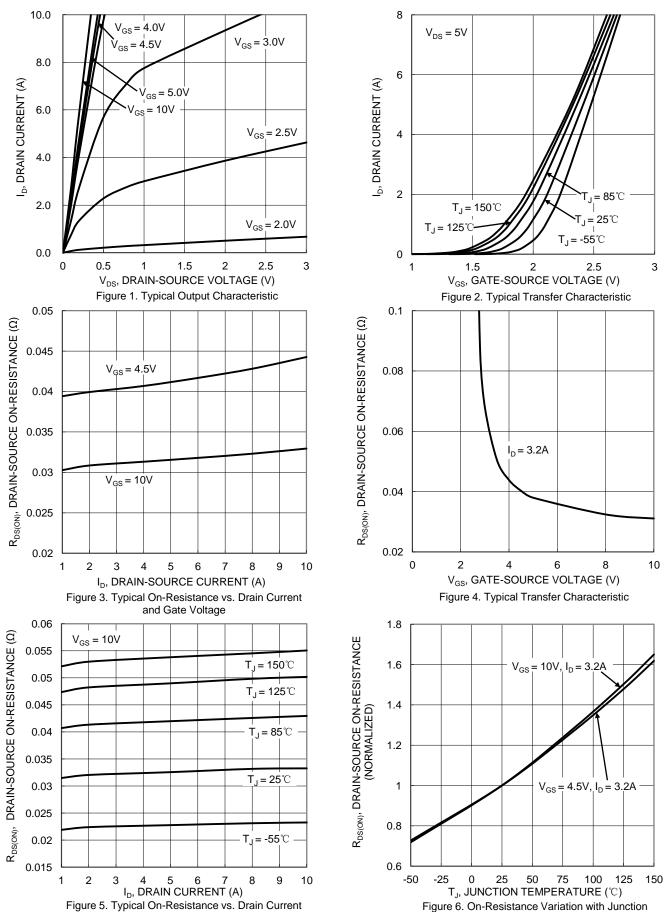
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	1	1	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance				65	mΩ	$V_{GS} = 10V, I_D = 3.2A$	
Static Diani-Source Off-Resistance	R _{DS(ON)}			75	11122	$V_{GS} = 4.5V, I_D = 3.2A$	
Diode Forward Voltage	V_{SD}	l	0.8	1.2	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)						_	
Input Capacitance	C_{iss}	_	190	_		\/ 45\/\/ 0\/	
Output Capacitance	Coss	_	36	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	-	26	_		1 – 1.01/11/12	
Gate Resistance	R_g	_	4.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	1	2.1	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	4.5	_	nC	V 45V L 4A	
Gate-Source Charge	Qgs	_	0.5	_	IIC	$V_{DS} = 15V, I_D = 4A$	
Gate-Drain Charge	Q_{gd}		0.8	_			
Turn-On Delay Time	t _{D(ON)}	_	1.7	_			
Turn-On Rise Time	t _R	_	5.7	_		$V_{DS} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	6.0	_	ns	$R_G = 3\Omega$, $I_D = 4A$	
Turn-Off Fall Time	t _F	_	1.6	_		, ,	
Reverse Recovery Time	t _{RR}	_	4.2	_	ns	1 40 41/44 4000/	
Reverse Recovery Charge	Q _{RR}	_	0.5	_	nC	I _F = 4A, di/dt = 100A/μs	

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.





and Junction Temperature

Temperature





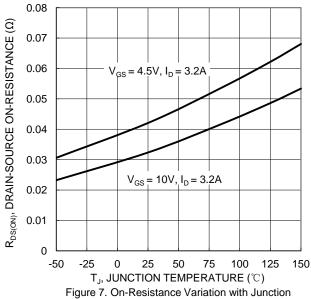


Figure 7. On-Resistance Variation with Junction Temperature

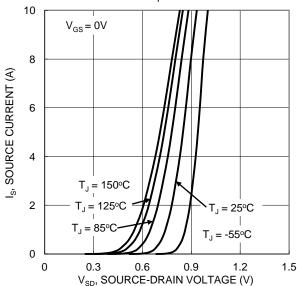


Figure 9. Diode Forward Voltage vs. Current

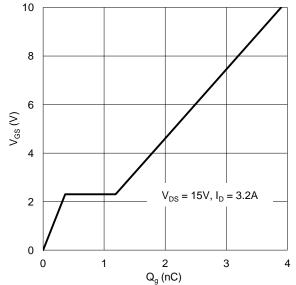


Figure 11. Gate Charge

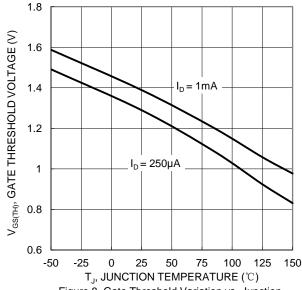
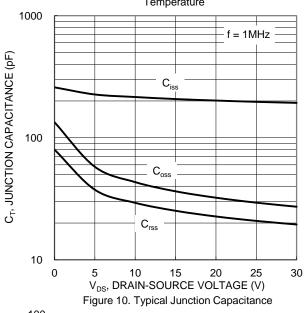
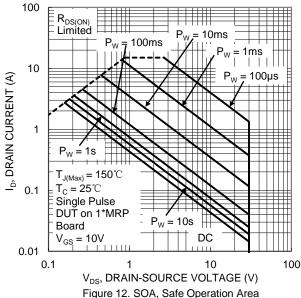


Figure 8. Gate Threshold Variation vs. Junction Temperature







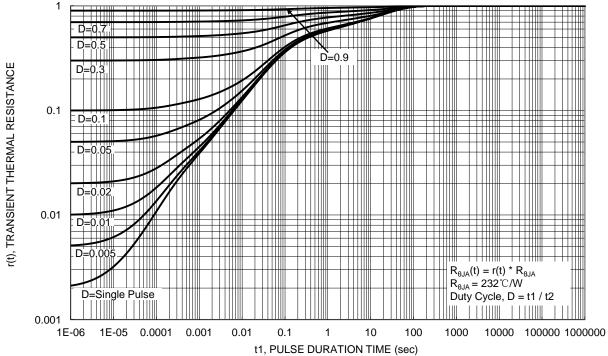


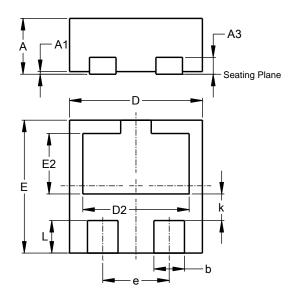
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-3

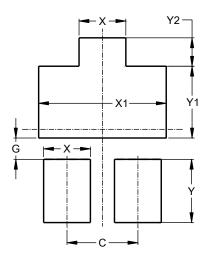


	X2-DF	N1010-3	3			
Dim	Min	Max	Тур			
Α	-	0.40	0.39			
A 1	0.00	0.05	0.02			
А3	-	-	0.13			
b	0.18	0.28	0.23			
D	0.95	1.05	1.00			
D2	0.70	0.90	0.80			
Е	0.95	1.05	1.00			
E2	0.36	0.56	0.46			
е	-	-	0.50			
k	-	-	0.20			
L	0.195	0.295	0.245			
Α	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-3



Dimensions	Value
2	(in mm)
С	0.500
G	0.150
Х	0.330
X1	0.900
Υ	0.445
Y1	0.505
Y2	0.200



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